## AMENDMENTS TO THE CLAIMS

## Claims 1-10 (Canceled)

- 11. (Original) A system for processing a semiconductor wafer with a gas having a chemical component, comprising:
  - a. a first enclosure defining a first chamber for receiving the semiconductor wafer and the gas; and
  - b. a scrubber comprising:
    - a second enclosure defining a second chamber for receiving at least a
      portion of the gas from said first chamber, said second enclosure having a
      gas inlet in fluid communication with said first chamber and said second
      chamber and a gas outlet in fluid communication with said second
      chamber; and
    - ii. at least one substrate contained within said second chamber and located between said gas inlet and said gas outlet, said substrate having a film deposition surface for receiving a film composed of the chemical component of the gas.
- 12. **(Original)** A system according to claim 11, further comprising a pump located between said first chamber and said second chamber for pumping the gas from said first chamber to said second chamber via said gas inlet.
- 13. **(Original)** A system according to claim 11, further comprising a heating element for heating at least one of said second enclosure and said at least one substrate.
- 14. **(Original)** A system according to claim 11, further comprising an abatement device for removing at least one component of the exhaust gas not deposited on said substrate.

## Claims 15-18 (Canceled)

- 19. (Original) A method for scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a first chemical component and a second chemical component, comprising the steps of:
  - a. flowing the exhaust gas through an enclosure defining a chamber and containing at least one substrate; and
  - b. causing the first chemical component to be chemical vapor deposited onto said at least one substrate.
- 20. (Original) A method according to claim 19, further comprising the step of removing the second chemical component from the exhaust gas after performing step b).
- 21. (Original) A method according to claim 19, wherein step b) is performed by heating at least one of said at least one substrate and said enclosure to at least 800°C.
- 22. (Original) A method according to claim 21, wherein step b) is performed by heating at least one of said at least one substrate and said enclosure to at least 1100°C.
- 23. (Original) A method according to claim 19, wherein the first chemical component is non-toxic and the second chemical component is toxic.
- 24. (Original) A method according to claim 23, wherein the first chemical component comprises silicon and the second chemical component comprises arsenic.
- 25. (Original) A method according to claim 19, further comprising after step b) the steps of:
  - a. removing said at least one substrate from said enclosure;
  - b. cleaning said at least one substrate of any film deposited thereon;
  - c. installing said at least one substrate in said enclosure; and
  - d. again causing the first chemical component to be chemical vapor deposited onto said at least one substrate.

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